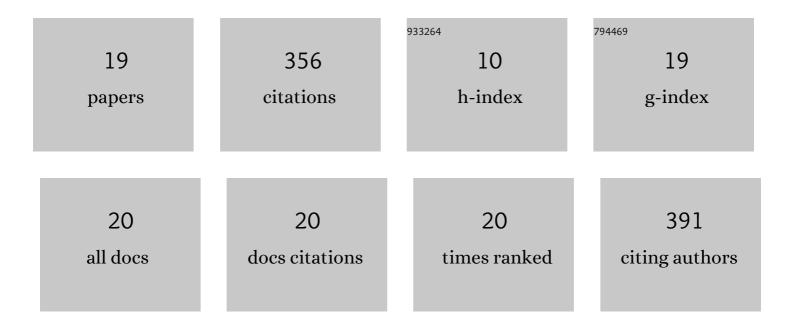
Erwine Pargon

List of Publications by Year in descending order

Source: https://exaly.com/author-pdf/5428920/publications.pdf Version: 2024-02-01



FOWINE PARCON

| # | Article | IF | CITATIONS |
|----|--|-----|-----------|
| 1 | Influence of the carrier wafer during GaN etching in Cl2 plasma. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2022, 40, 023202. | 0.9 | 6 |
| 2 | Anisotropic and low damage III-V/Ge heterostructure etching for multijunction solar cell fabrication with passivated sidewalls. Micro and Nano Engineering, 2021, 11, 100083. | 1.4 | 7 |
| 3 | Suppression of Parasitic Nonlinear Processes in Spontaneous Four-Wave Mixing with Linearly Uncoupled Resonators. Physical Review Letters, 2021, 127, 033901. | 2.9 | 11 |
| 4 | Photoluminescence mapping of the strain induced in InP and GaAs substrates by SiN stripes etched from thin films grown under controlled mechanical stress. Thin Solid Films, 2020, 706, 138079. | 0.8 | 4 |
| 5 | Mechanical stress in InP and GaAs ridges formed by reactive ion etching. Journal of Applied Physics, 2020, 128, 225705. | 1.1 | 2 |
| 6 | New route for selective etching in remote plasma source: Application to the fabrication of horizontal stacked Si nanowires for gate all around devices. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2019, 37, . | 0.9 | 10 |
| 7 | Two-step cycling process alternating implantation and remote plasma etching for topographically selective etching: Application to Si3N4 spacer etching. Journal of Applied Physics, 2019, 126, . | 1.1 | 13 |
| 8 | Ultralow-loss tightly confining Si ₃ N ₄ waveguides and high-Q microresonators. Optics Express, 2019, 27, 30726. | 1.7 | 85 |
| 9 | Improvement of Sidewall Roughness of Submicron SOI Waveguides by Hydrogen Plasma and Annealing. IEEE Photonics Technology Letters, 2018, 30, 591-594. | 1.3 | 34 |
| 10 | Low damage patterning of In0.53Ga0.47As film for its integration as n-channel in a fin metal oxide semiconductor field effect transistor architecture. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2018, 36, . | 0.9 | 5 |
| 11 | Mapping of mechanical strain induced by thin and narrow dielectric stripes on InP surfaces. Optics Letters, 2018, 43, 3505. | 1.7 | 7 |
| 12 | Spectral analysis of sidewall roughness during resist-core self-aligned double patterning integration. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2016, 34, 051807. | 0.6 | 4 |
| 13 | Smoothing mechanisms involved in thermal treatment for linewidth roughness reduction of 193-nm photoresist patterns. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2013, 31, 061203. | 0.6 | 5 |
| 14 | Atomic-scale silicon etching control using pulsed Cl2 plasma. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2013, 31, . | 0.6 | 17 |
| 15 | Benefits of plasma treatments on critical dimension control and line width roughness transfer during gate patterning. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2013, 31, 012205. | 0.6 | 30 |
| 16 | Silicon recess minimization during gate patterning using synchronous plasma pulsing. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2012, 30, . | 0.6 | 25 |
| 17 | HBr Plasma Treatment Versus VUV Light Treatment to Improve 193 nm Photoresist Pattern Linewidth Roughness. Plasma Processes and Polymers, 2011, 8, 1184-1195. | 1.6 | 25 |
| 18 | 193nm resist chemical modification induced by HBr cure plasma treatment: a TD-GC/MS outgassing study. Proceedings of SPIE, 2011, , . | 0.8 | 3 |

| # | Article | IF | CITATIONS |
|----|---|-----|-----------|
| 19 | Reducing damage to Si substrates during gate etching processes by synchronous plasma pulsing. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2010, 28, 926-934. | 0.6 | 63 |